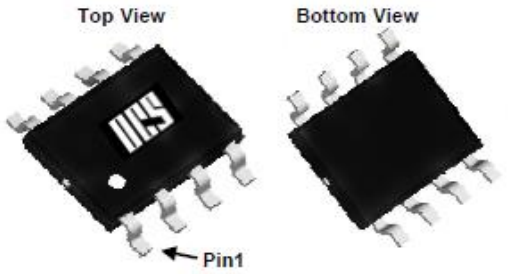
■ General Description

The OCM4606S uses advanced trench technology to provide excellent RDS(ON)and low gate charge . The complementary MOSFET may be used to form a level shifted high side switch, and for a host of other applications.



Marking and Pin assignment

■ General Features

N-Channel

V_{DS}= 30V, I_D=6.5A

$R_{DS(ON)}$<25m Ω@ V_{GS}=10V

$R_{DS(ON)}$<36m Ω@ V_{GS}=4.5V

P-Channel

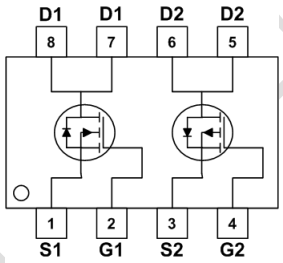
V_{DS}= -30V, I_D=-6.0A

$R_{DS(ON)}$<30m Ω@ V_{GS}=-10V

$R_{DS(ON)}$<48m Ω@ V_{GS}=-4.5V

■ Application

- High power and current handing capability
- BLDC
- Others application



Schematic diagram

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	30	-30	V
Gate-Source Voltage		V_{GS}	±20	±20	V
Continuous Drain Current	T_A=25℃	ID	6.5	-6.0	A
	T_A=70℃		5.5	-5.0	
Pulsed Drain Current (Note 2)		I_{DM}	30	-30	A
Single Pulse Avalanche(Note 3)		EAS	8.1	45	mJ
Avalanche Current		I_{AS}	12.7	-30	A
Maximum Power Dissipation(Note4)	T_A=25℃	PD	1.5	1.5	W
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55 To 150	-55 To 150	℃

Thermal Characteristic

Parameter	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient(Note 1)	$R_{\theta JA}$	85	℃/W
Thermal Resistance, Junction-to-Case(Note 1)	$R_{\theta JC}$	60	℃/W